

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A manufacturing method of a semiconductor device comprising:

forming a plurality of circuit portions each having a modulation circuit, a demodulation circuit, and a logic circuit over an insulating substrate by using a first exposure means having any one of a mirror projection exposure system, a step and repeat exposure system and a step and scan exposure system; and

forming a plurality of different memory circuits over the substrate by using a second exposure means capable of changing an exposure pattern depending on program.

2. (Currently Amended) A manufacturing method of a semiconductor device comprising:

forming an object to be processed over an insulating substrate;

applying a photoresist on the object;

exposing the photoresist by a first exposure means having any one of a mirror projection exposure system, a step and repeat exposure system and a step and scan exposure system;

exposing the photoresist by a second exposure means capable of changing an exposure pattern depending on program;

developing the photoresist exposed by the first exposure means and the second exposure means; and

etching the object by using the developed photoresist to form a plurality of first patterns of circuit portions each having a modulation circuit, a demodulation circuit, and a logic circuit and a plurality of second patterns of different memory circuits.

3. (Currently Amended) A manufacturing method of a semiconductor device comprising:

forming an object to be processed over an insulating substrate;

applying a first photoresist on the object;

exposing the first photoresist by a first exposure means having any one of a mirror projection exposure system, a step and repeat exposure system and a step and scan exposure system;

developing the exposed first photoresist;

etching the object by using the developed first photoresist to form a plurality of first patterns of circuit portions each having a modulation circuit, a demodulation circuit, and a logic circuit;

applying a second photoresist on the object;

exposing the second photoresist by a second exposure means capable of changing an exposure pattern depending on program;

developing the exposed second photoresist; and

etching the object by using the developed second photoresist to form a plurality of second patterns of different memory circuits.

4. (Currently Amended) A manufacturing method of a semiconductor device comprising:

forming an object to be processed over an insulating substrate;

applying a photoresist on the object;

exposing the photoresist by a first exposure means having any one of a mirror projection exposure system, a step and repeat exposure system and a step and scan exposure system;

exposing the photoresist by a second exposure means capable of changing an exposure pattern depending on program;

developing the photoresist exposed by the first exposure means and the second exposure means; and

etching the object by using the developed photoresist to form a plurality of first patterns of first circuit portions and a plurality of second patterns of different second circuit portions,

~~wherein the second exposure means can change the contents of exposure depending on program.~~

5. (Currently Amended) A manufacturing method of a semiconductor device comprising:

forming an object to be processed over an insulating substrate;

applying a photoresist on the object;

exposing the photoresist by a first exposure means having any one of a mirror projection exposure system, a step and repeat exposure system and a step and scan exposure system;

exposing the photoresist by a second exposure means capable of changing an exposure pattern depending on program;

developing the photoresist exposed by the first exposure means and the second exposure means; and

etching the object by using the developed photoresist to form a plurality of first patterns of first circuit portions and a plurality of second patterns of different second circuit portions,

wherein different data is stored in each of the second circuit portions.

6. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 3, wherein the memory circuit is a mask ROM.

7. (Original) The manufacturing method of a semiconductor device according to claim 4 or 5, wherein the second circuit portion is a mask ROM.

8. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 3, wherein the difference among the plurality of memory circuits is data stored therein.

9. (Original) The manufacturing method of a semiconductor device according to claim 4, wherein the difference among the plurality of second circuit portions is data stored therein.

10.-13. (Canceled)

14. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 5, wherein the second exposure means is an exposure means using an electron beam exposure system.

15. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 5, wherein the second exposure means is an exposure means using a laser exposure system.

16. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 5, wherein a portion exposed by the second exposure means is a contact hole.

17. (Original) The manufacturing method of a semiconductor device according to any one of claims 1 to 5, wherein the insulating substrate is one selected from the group consisting of a glass substrate, a plastic substrate, and a film insulator.

18. (Canceled)

19. (Original) The manufacturing method of a semiconductor device according to claim 4 or 5, wherein each of the first circuit portions comprises a modulation circuit, a demodulation circuit, and a logic circuit.

20. (Original) The manufacturing method of a semiconductor device according to claim 4 or 5, wherein each of the second circuit portions comprises different memory circuits.